BT137-600D



4Q Triac

Rev. 3 — 24 March 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

1.3 Applications

General purpose motor control

General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 600 | V |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u> | - | - | 65 | Α |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 102 \text{ °C}$; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u> | - | - | 8 | Α |



Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|-------------------------|--|-----|-----|-----|------|
| Static characteristics | | | | | | |
| 0. | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ C}}$ | - | 2.5 | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ C}}$ | - | 3.5 | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G\text{-};$ $T_j = 25 ^{\circ}\text{C; see } \frac{\text{Figure 7}}{}$ | - | 3.5 | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$ | - | 6.5 | 10 | mA |
| I _H | holding current | $V_D = 12 \text{ V; } T_j = 25 \text{ °C;}$ see Figure 9 | - | 1.5 | 10 | mA |

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | | N.1 |
| 2 | T2 | main terminal 2 | mb | T2—T1 |
| 3 | G | gate | | sym051 |
| mb | T2 | mounting base; main terminal 2 | 1 2 3 | |
| | | | SOT78 (TO-220AB) | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|----------|--|---------|
| | Name | Description | Version |
| BT137-600D | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|--|-----|-----|--------|
| V_{DRM} | repetitive peak off-state voltage | | - | 600 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; T _{mb} ≤ 102 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u> | - | 8 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5 | - | 65 | Α |
| | | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$ | - | 71 | Α |
| I ² t | I ² t for fusing | $t_p = 10 \text{ ms}$; sine-wave pulse | - | 21 | A^2s |
| dl _T /dt | rate of rise of on-state current | I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+ | - | 50 | A/µs |
| | | $I_T = 12 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; $T2+ G-$ | - | 50 | A/µs |
| | | $I_T = 12 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G- | - | 50 | A/µs |
| | | $I_T = 12 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G+ | - | 10 | A/µs |
| I _{GM} | peak gate current | | - | 2 | Α |
| V_{GM} | peak gate voltage | | - | 5 | V |
| P _{GM} | peak gate power | | - | 5 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| Tj | junction temperature | | - | 125 | °C |

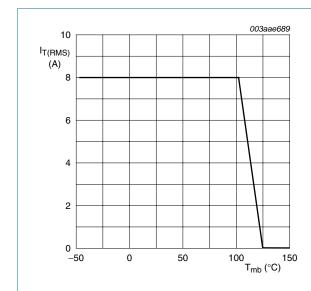
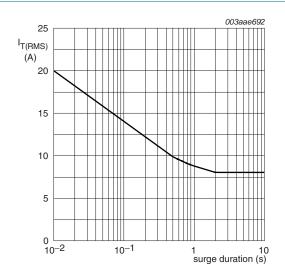


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



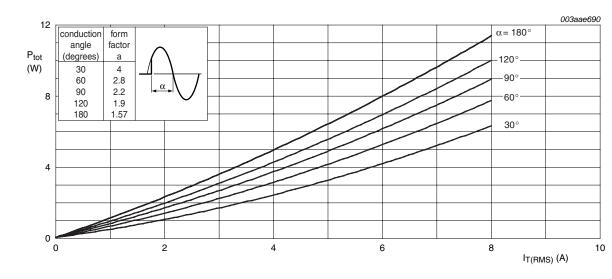
f = 50 Hz $T_{mb} \le 102 \text{ °C}$

Fig 2. RMS on-state current as a function of surge duration; maximum values

BT137-600D

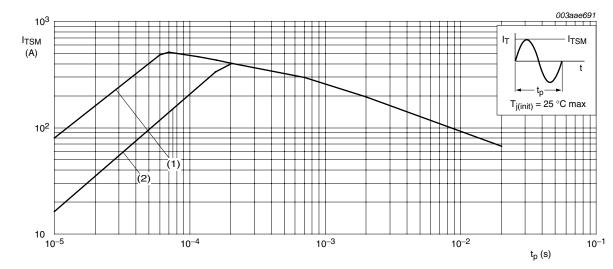
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 α = conduction angle

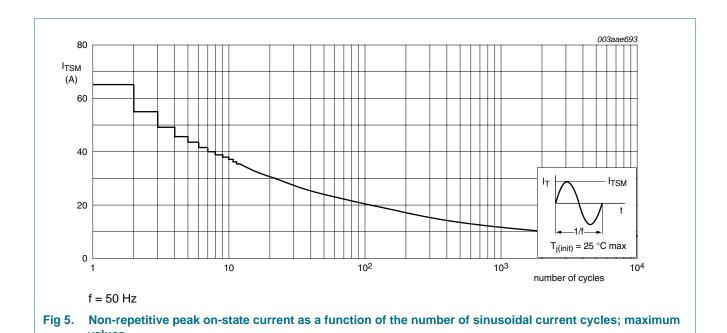
Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



t_p ≤ 20 ms

- (1) dI_T/dt limit
- (2) T2- G+ quadrant limit

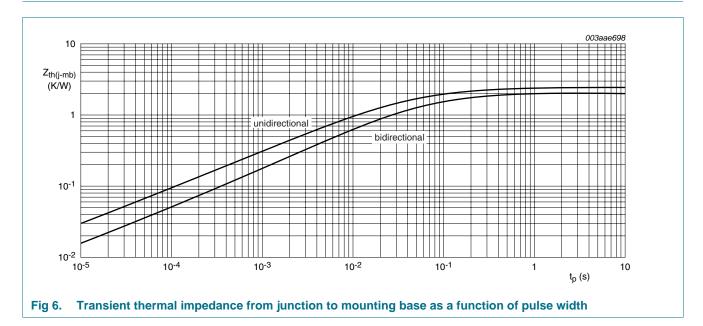
Fig 4. Non-repetitive peak on-state current as a function of pulse width; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

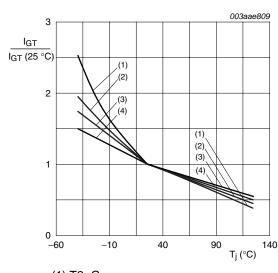
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from | half cycle; see Figure 6 | - | - | 2.4 | K/W |
| | junction to mounting base | full cycle; see Figure 6 | - | - | 2 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |



6. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|---|------|-----|------|------|
| Static cha | racteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } 100 \text{ C}}$ | - | 2.5 | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ c}}$ | - | 3.5 | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G\text{-};$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$ | - | 3.5 | 5 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$ | - | 6.5 | 10 | mA |
| IL | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$ | - | 1.6 | 15 | mA |
| | | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{\text{ V}}$ | - | 8.5 | 20 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$ | - | 1.2 | 15 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$ | - | 2.5 | 20 | mA |
| l _H | holding current | V _D = 12 V; T _j = 25 °C; see <u>Figure 9</u> | - | 1.5 | 10 | mΑ |
| V _T | on-state voltage | I _T = 10 A; T _j = 25 °C; see <u>Figure 10</u> | - | 1.3 | 1.65 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11 | - | 0.7 | 1.5 | V |
| | | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11 | 0.25 | 0.4 | - | V |
| I _D | off-state current | V _D = 600 V; T _j = 125 °C | - | 0.1 | 0.5 | mΑ |
| Dynamic | characteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 402 V; T_j = 125 °C; R_{GT1} = 1 k Ω ; exponential waveform; gate open circuit | - | 5 | - | V/µs |
| t _{gt} | gate-controlled turn-on time | $I_{TM} = 12 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ mA};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$ | - | 2 | - | μs |



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

tion of Fig 8.

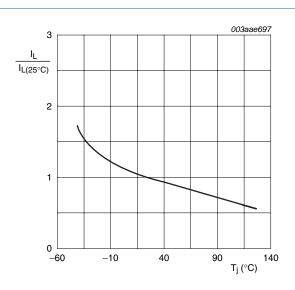


Fig 7. Normalized gate trigger current as a function of junction temperature



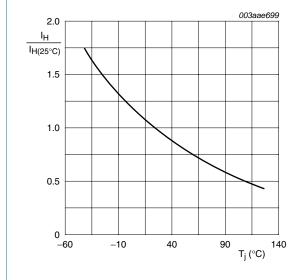
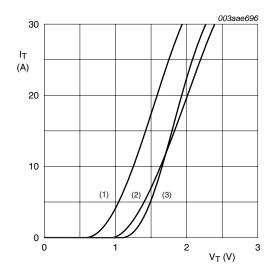


Fig 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.264 \text{ V}$

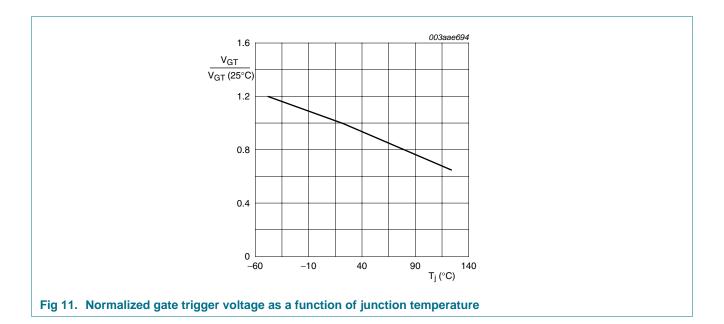
 $R_s = 0.038 \Omega$

(1) T_i = 125 °C; typical values

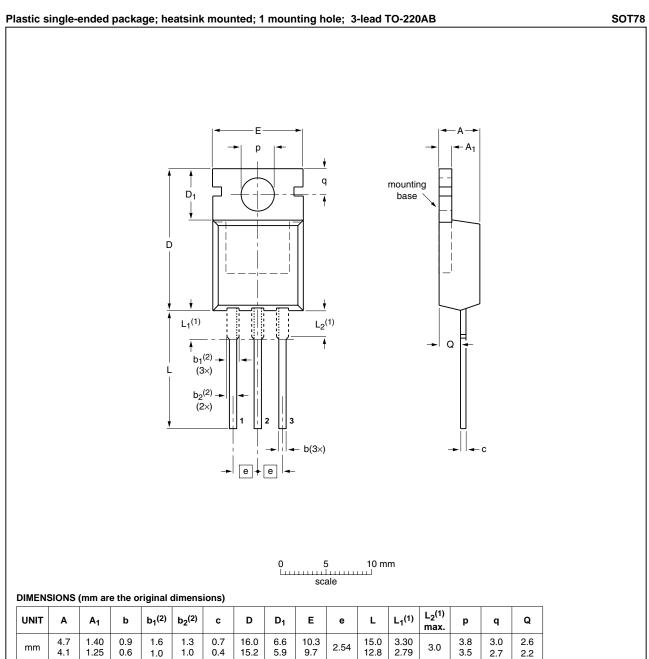
(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



7. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|-----------------|-------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

Fig 12. Package outline SOT78 (TO-220AB)

BT137-600D

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|------------------------------------|----------------------------|-------------------------|-------------------------------|
| BT137-600D v.3 | 20110324 | Product data sheet | - | BT137-600D_2 |
| Modifications: | | | designed to comply with | n the new identity guidelines |
| | Legal texts ha | ve been adapted to the new | company name where | appropriate. |
| BT137-600D_2 | 20010601 | Product specification | - | BT137_SERIES_D_1 |

9. Legal information

9.1 Data sheet status

| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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11. Contents

| 1 | Product profile |
|-----|--------------------------|
| 1.1 | General description |
| 1.2 | Features and benefits1 |
| 1.3 | Applications |
| 1.4 | Quick reference data1 |
| 2 | Pinning information |
| 3 | Ordering information |
| 4 | Limiting values |
| 5 | Thermal characteristics5 |
| 6 | Characteristics6 |
| 7 | Package outline |
| 8 | Revision history10 |
| 9 | Legal information11 |
| 9.1 | Data sheet status |
| 9.2 | Definitions11 |
| 9.3 | Disclaimers |
| 9.4 | Trademarks12 |
| 10 | Contact information |

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